



# Dynamics of polaritons in semiconductor microcavities near instability thresholds

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## ABSTRACT

A theoretical study is presented on the dynamics of polaritons in semiconductor microcavities near parametric instability thresholds. With upward or downward ramp of optical pump, different instability modes emerge in parameter space defined by damping and detuning. According to these modes, stationary short-wave, stationary periodic, oscillatory periodic, and oscillatory uniform parametric instabilities are distinguished. By multiple scale expansion, the dynamics near threshold can be described by a critical mode with a slowly varying amplitude for the last three instabilities. Furthermore, it is found that the evolutions of their amplitudes are governed by real or complex Ginzburg–Landau equations.

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## 1. Introduction

Polaritons in the semiconductor microcavity form a strongly nonequilibrium system with cubic nonlinearity, which is of fundamental importance and application promise [1]. Cavity polaritons are coupled modes of cavity photons and excitons. The photonic component ensures easy adjustability and detection, while the excitonic component provides a strong interaction between polaritons. These unique features make some interesting phenomena possible, such as polariton Bose–Einstein condensation [2–4] and superfluid [5,6], optical bistability [7], soliton [8–10] and vortex excitations [11,12], parametric amplification and oscillation [13–17], etc.

In the semiconductor microcavity, parametric oscillation is a process that generates coherent signal and idler modes from a pair of pumping polaritons. Comparing with the optical counterpart, polariton parametric oscillator possesses much richer dynamics due to the cubic nonlinearity. There have some experimental and theoretic investigations on this aspect. For example, observation of parametric oscillation has been reported [13–15]. A classical model was proposed to treat the amplifier and oscillator unitively [16]. The threshold behavior was discussed on the basis of three-mode theory [17].

As nonequilibrium dissipative systems, polaritons in semiconductor microcavity can be used to study pattern formation outside

of equilibrium [18]. With lower energy pump, there exist ground states (trivial or inhomogeneous stationary solutions). If increasing pump, possible instabilities lead to a variety of pattern formation. The dynamics of the patterns close to the instability threshold can be separated into a fast component (with the temporal and spatial scales set by the critical frequency and wave number respectively) and an envelope that varies slowly in space and time. This can be done by multiple scale expansion. In general, the solution near threshold is a plane-wave critical mode with a slowly varying amplitude. The amplitude satisfies nonlinear partial differential equations. This perturbation method has been used to analyze the parametric conversion process and nonlinear behavior near parametric threshold in optical parametric oscillators [19–21]. Enlightened by the similarity between optical and polariton parametric oscillators, we apply multiple scale expansion on the cavity polariton system to study the dynamics near instability thresholds.

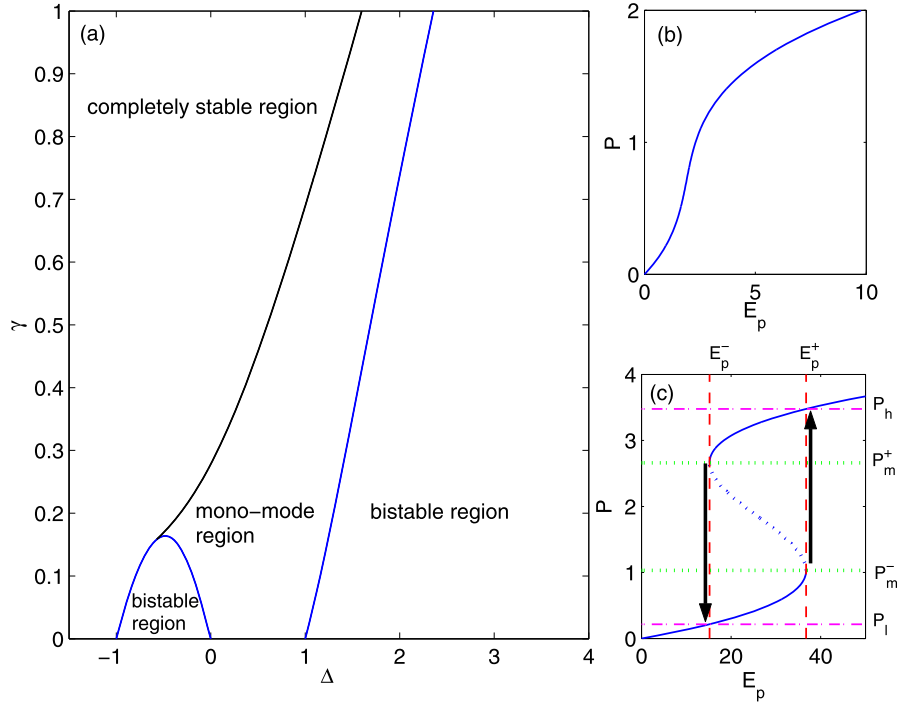
In this Letter, two kinds of pump-like modes, mono-mode and bistable mode, are analyzed. By stability analysis, different instabilities are classified in parameter plane. The lower and upper thresholds are obtained. The neutral stability surfaces are illuminated simply. Applying multiple scale expansion near the instability thresholds, three kinds of signal–idler pairs and their amplitude equations are introduced as the solutions and solvability condition of a hierarchy of equations.

## 2. Pump-like mode

Considering the spatially homogeneous pump  $\mathcal{E}_p e^{-i\omega_p t}$ , the polariton behavior in semiconductor cavity is described by the dimensionless equations [5,8,11],

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**Fig. 1.** (Color online.) (a) Mono-mode and bistable regions. (b) Mono-mode. Here,  $\Delta = 1.6017$  and  $\gamma = 0.6558$ . (c) Bi-stability. Here,  $\Delta = 3.0789$  and  $\gamma = 0.6818$ . The bistable state exists between  $E_p^+$  and  $E_p^-$  which are denoted by the vertical dashed lines. The middle dotted branch is unstable. The horizontal dotted lines denote  $P_m^+$  and  $P_m^-$ . The horizontal dash-dotted lines denote  $P_h$  and  $P_l$ .

$$i\partial_t E + \left( \frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} \right) E + (i\gamma + \Delta)E + \psi = i\mathcal{E}_p, \quad (1)$$

$$i\partial_t \psi + (i\gamma + \Delta)\psi + E = |\psi|^2 \psi.$$

Here, the spatial and temporal coordinates are rescaled by  $\sqrt{v/(2k_z\Omega_R)}$  and  $1/\Omega_R$  respectively, where  $\Omega_R$  is the Rabi frequency,  $v$  is the light speed in the semiconductor, and  $k_z$  is the quantized photon momentum along the growth direction. The photon and exciton fields are normalized by  $\sqrt{\Omega_R/g}$  with  $g$  being the interaction constant between excitons.  $\gamma$  are the damping constants normalized to  $\Omega_R$ .  $\Delta = (\omega_p - \omega_r)/\Omega_R$  represents the detuning of the pumping frequency  $\omega_p$  from the identical resonance frequency of exciton and cavity  $\omega_r$ . The squared amplitude of external pump is normalized by  $\Omega_R^3/g$ . The photon and exciton fields are described as  $\mathcal{E} = Ee^{-i\omega_p t}$  and  $\Psi = \psi e^{-i\omega_p t}$ .

With proper pump intensity, the polariton field simply oscillates with the same frequency and wave vector as pump. Under the spatially homogeneous pump ( $k_p = 0$ ), these modes are determined by

$$(i\gamma + \Delta)E_0 + \psi_0 = i\mathcal{E}_p, \quad (2)$$

$$(i\gamma + \Delta)\psi_0 + E_0 = |\psi_0|^2 \psi_0.$$

Considering the structure of this equation, the phase factor of  $\psi_0$  can be incorporated into the pumping term by transformation. And that, only  $|\psi_0|^2$  is considered as the density of pump-like polariton. So, it is reasonable to assume that  $\psi_0$  is real ( $\psi_0 = p$ ). By eliminating  $E_0$  from Eqs. (2), one can get a cubic equation about the square modulus of  $\psi_0$ ,  $(\gamma^2 + \Delta^2)P^3 - 2\Delta(\gamma^2 + \Delta^2 - 1)P^2 + [(\gamma^2 + \Delta^2 + 1)^2 - 4\Delta^2]P - E_p = 0$ , where  $P = p^2$ , and  $E_p = |\mathcal{E}_p|^2$ . The type of the roots determines the properties of pump-like modes. By algebraic analysis and considering  $P$  and  $E_p$  are positive, one can find that three real roots exist in regions  $\Sigma_0 > 0$ ,  $E_p^- < E_p < E_p^+$  and  $-1 < \Delta < 0$  or  $\Delta > 1$ , where  $E_p^\pm = (f \pm 2\sqrt{\Sigma_0^3})/[27(\gamma^2 + \Delta^2)^2]$ , with  $\Sigma_0 = \Delta^2(\gamma^2 + \Delta^2 - 1)^2 -$

$3\gamma^2(\gamma^2 + \Delta^2 + 1)^2$  and  $f = 2\Delta(\gamma^2 + \Delta^2 - 1)[\Delta^2(\gamma^2 + \Delta^2 - 1)^2 + 9\gamma^2(\gamma^2 + \Delta^2 + 1)^2]$ . Otherwise, there exists one real root. The one real root corresponds to a mono-mode excited by pump (shown in Fig. 1(b)), while, the three real roots represent the bistable state (shown in Fig. 1(c)). The regions of these states in  $\Delta$ - $\gamma$  plane are shown in Fig. 1(a).

As depicted in Fig. 1(c), these three real roots form a hysteresis loop. It has been verified experimentally that the system is in the bistable state here [7,17]. The turning points of the hysteresis loop are  $P_m^\pm = [2\Delta(\Delta^2 + \gamma^2 - 1) \pm \sqrt{\Sigma_0}]/[3(\Delta^2 + \gamma^2)]$ , which can be obtained by  $dE_p/dP = 0$ . The intermediate part between  $P_m^-$  and  $P_m^+$  is unstable, named as single-mode instability [5,17]. Therefore, when  $E_p^- < E_p < E_p^+$  (or  $P_l < P < P_h$ ), the multiple states excited by pump in zeroth-order system must be considered. The hysteresis loop starts at  $P_l$  and ends at  $P_h$ , where  $P_{h,l} = 2[\Delta(\Delta^2 + \gamma^2 - 1) \pm \sqrt{\Sigma_0}]/[3(\Delta^2 + \gamma^2)]$ . With upward ramp of pump, the polariton density jumps from  $P_m^-$  to  $P_h$  at  $E_p = E_p^+$ , while from  $P_m^+$  to  $P_l$  at  $E_p = E_p^-$  for downward ramp, as shown by the arrows in Fig. 1(c).

### 3. Parametric threshold and neutral stability surface

#### 3.1. Stability analysis

With upward or downward ramp of pump, the pump-like mode will be destroyed possibly. By linear stability analysis, the instability thresholds and the unstable modes can be well studied. Meanwhile, the completely stable region and different kinds of parametric instabilities can be distinguished.

Assuming  $E = E_0 + E'$ , and  $\psi = \psi_0 + \psi'$ , where  $E'$  and  $\psi'$  are responses for small perturbation, it can be obtained by linearization that

$$\frac{\partial \mathbf{V}'}{\partial t} + \hat{L}\mathbf{V}' = 0, \quad (3)$$

where

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